

# MOS FIELD EFFECT TRANSISTOR 2SK3299

# SWITCHING N-CHANNEL POWER MOS FET INDUSTRIAL USE

#### **DESCRIPTION**

The 2SK3299 is N-Channel MOS FET device that features a low gate charge and excellent switching characteristics, designed for high voltage applications such as switching power supply, AC adapter.

# **ORDERING INFORMATION**

PART NUMBER	PACKAGE		
2SK3299	TO-220AB		
2SK3299-S	TO-262		
2SK3299-ZJ	TO-263		

#### **FEATURES**

- •Low gate charge
- $Q_G = 34$  nC TYP. ( $V_{DD} = 450$  V,  $V_{GS} = 10$  V,  $I_D = 10$  A)
- •Gate voltage rating ±30 V
- •Low on-state resistance

 $R_{DS(on)} = 0.75 \Omega MAX. (Vgs = 10 V, ID = 5.0 A)$ 

- Avalanche capability ratings
- •Surface mount package available

#### ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage (Vgs = 0 V)	VDSS	600	V
Gate to Source Voltage (Vps = 0 V)	Vgss	±30	V
Drain Current (DC) (Tc = 25°C)	I <sub>D(DC)</sub>	±10	Α
Drain Current (Pulse) Note1	ID(pulse)	±40	Α
Total Power Dissipation (T <sub>A</sub> = 25°C)	P <sub>T1</sub>	1.5	W
Total Power Dissipation (Tc = 25°C)	P <sub>T2</sub>	75	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C
Single Avalanche Current Note2	las	10	Α
Single Avalanche Energy Note2	Eas	66.7	mJ

**Notes 1.** PW  $\leq$  10  $\mu$ s, Duty Cycle  $\leq$  1%

2. Starting T<sub>ch</sub> = 25°C, V<sub>DD</sub> = 150 V, R<sub>G</sub> = 25  $\Omega$ , V<sub>GS</sub> = 20 V  $\rightarrow$  0 V

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Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

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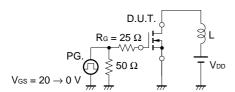
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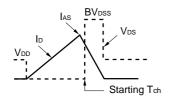


**ELECTRICAL CHARACTERISTICS(TA = 25°C)** 

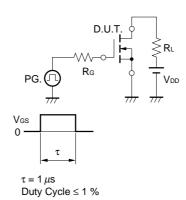
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Drain Leakage Current	Ioss	Vps = 600 V, Vgs = 0 V			100	μΑ
Gate Leakage Current	Igss	Vgs = ±30 V, Vps = 0 V			±100	nA
Gate Cut-off Voltage	V <sub>G</sub> S(off)	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	2.5		3.5	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 5.0 A	3.2			S
Drain to Source On-state Resistance	RDS(on)	Vgs = 10 V, ID = 5.0 A		0.68	0.75	Ω
Input Capacitance	Ciss	Vps = 10 V		1580		pF
Output Capacitance	Coss	Vgs = 0 V		280		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		25		pF
Turn-on Delay Time	td(on)	VDD = 150 V, ID = 5.0 A		27		ns
Rise Time	tr	V <sub>GS(on)</sub> = 10 V		17		ns
Turn-off Delay Time	td(off)	R <sub>G</sub> = 10 Ω		66		ns
Fall Time	tf			24		ns
Total Gate Charge	Q <sub>G</sub>	V <sub>DD</sub> = 450 V		34		nC
Gate to Source Charge	Qgs	Vgs = 10 V		8.2		nC
Gate to Drain Charge	Q <sub>GD</sub>	ID = 10 A		12.3		nC
Diode Forward Voltage	V <sub>F(S-D)</sub>	IF = 10 A, VGS = 0 V		1.0		V
Reverse Recovery Time	trr	IF = 10 A, VGS = 0 V		1.9		μs
Reverse Recovery Charge	Qrr	di/dt = 50 A/μs		12		μC

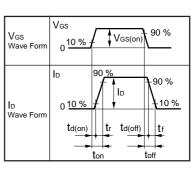
# **TEST CIRCUIT 1 AVALANCHE CAPABILITY**





#### **TEST CIRCUIT 2 SWITCHING TIME**

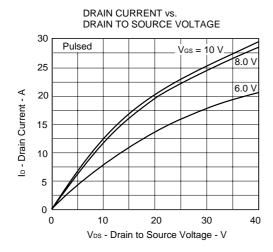


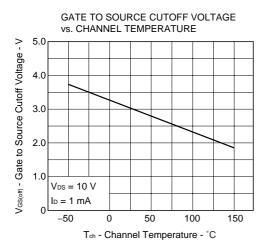


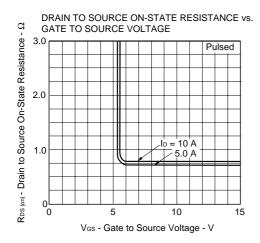
# **TEST CIRCUIT 3 GATE CHARGE**



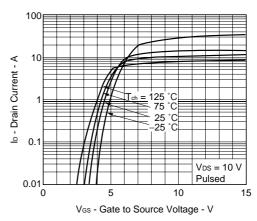
# **★** TYPICAL CHARACTERISTICS (TA = 25 °C)



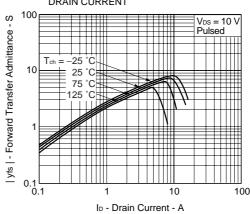


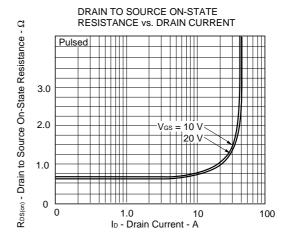


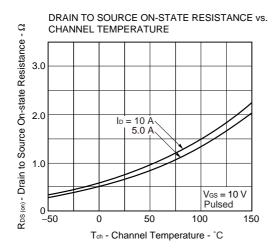
# FORWARD TRANSFER CHARACTERISTICS

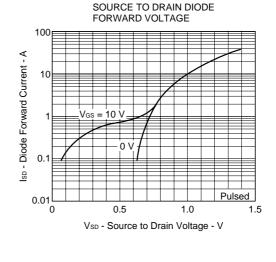


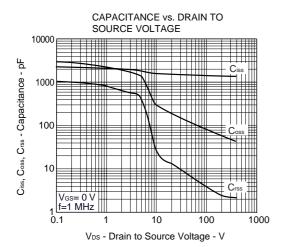
# FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT

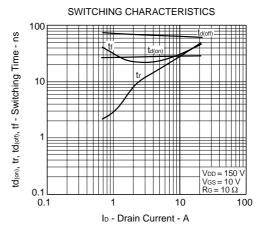


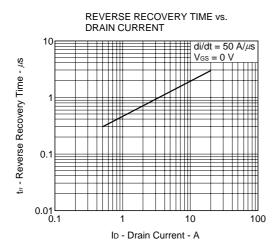


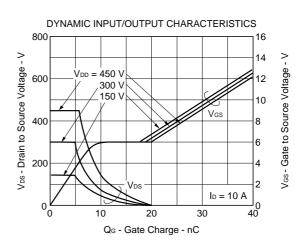




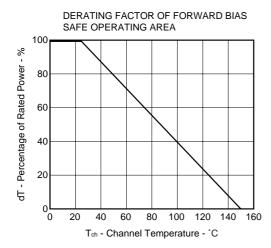


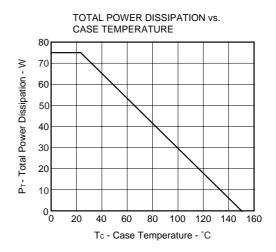


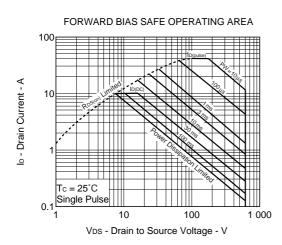




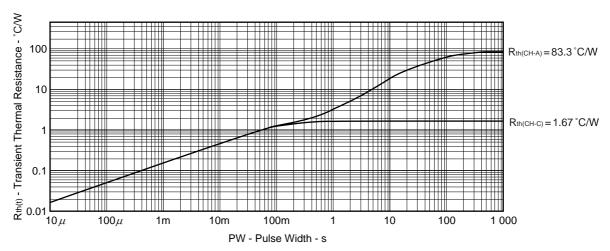


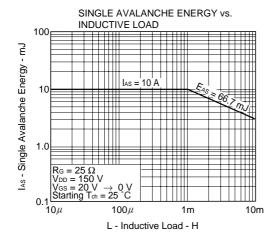


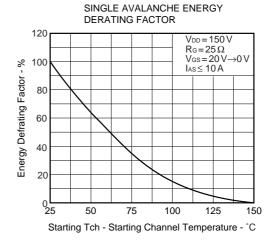




#### TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



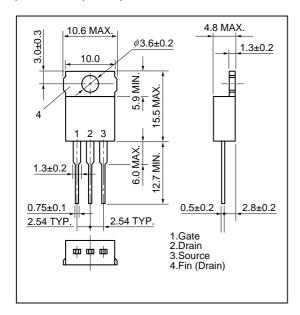




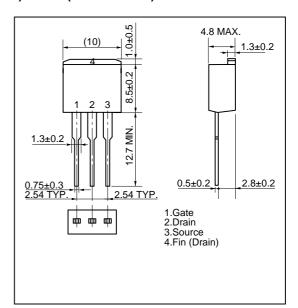


### PACKAGE DRAWINGS (Unit: mm)

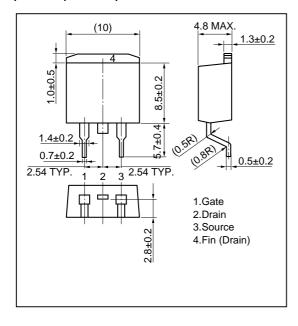
# 1)TO-220AB (MP-25)



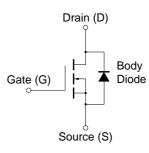
# 2)TO-262 (MP-25 Fin Cut)



#### 3)TO-263 (MP-25ZJ)



#### **EQUIVALENT CIRCUIT**



**Remark** Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

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